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forming a groove in a top surface of said base region at a portion thereof;
forming spacers on sidewalls of said groove;
forming a diffusion source film in said bottom surface of said groove to be embedded therein between said spacers; and
forming an emitter region of said first conductivity type in said base region at a bottom surface of said groove, said emitter region being formed in said top surface of said base region at a bottom of said diffusion source film between said spacers.

1

Kindly cancel claims 2 and 5 presently pending in this application without prejudice.

Kindly amend claim 6 as follows.

A2

6. (Amended) A method of manufacturing a semiconductor device according to claim 1, further comprising:
forming a base electrode on said top surface of said base region around said portion of said groove; and
an emitter electrode on said surface of said diffusion source film.
